

MM9Z2V2B~MM9Z39B

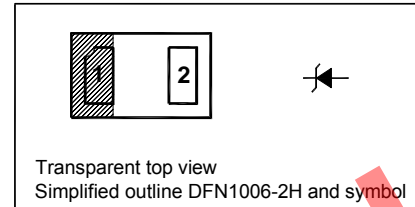
SILICON PLANAR ZENER DIODES

Features

- Total power dissipation: max. 100 mW
- Small plastic package suitable for surface mounted design
- High reliability

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

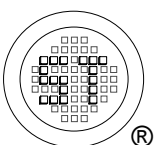


Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Power Dissipation	P_{tot}	100	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{Stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 10\text{ mA}$	V_F	0.9	V



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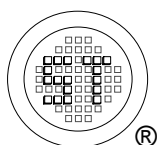


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Characteristics at $T_a = 25^\circ\text{C}$

Type	Marking Code	Zener Voltage ¹⁾			Dynamic Resistance		Leakage Current	
		V_{ZT}		at I_{ZT}	Z_{ZT}	at I_{ZT}	I_R	at V_R
		Min. (V)	Max. (V)	(mA)	Max. (Ω)	(mA)	Max. (μA)	(V)
MM9Z2V2B	8A	2.1	2.4	5	100	5	120	0.7
MM9Z2V4B	8B	2.3	2.65	5	100	5	120	1
MM9Z2V7B	8C	2.65	2.95	5	110	5	120	1
MM9Z3V0B	8D	2.95	3.25	5	120	5	50	1
MM9Z3V3B	8E	3.25	3.55	5	120	5	20	1
MM9Z3V6B	8F	3.6	3.845	5	100	5	10	1
MM9Z3V9B	8G	3.89	4.16	5	100	5	5	1
MM9Z4V3B	8H	4.17	4.43	5	100	5	5	1
MM9Z4V7B	8J	4.55	4.75	5	100	5	2	1
MM9Z5V1B	8K	4.98	5.2	5	80	5	2	1.5
MM9Z5V6B	8L	5.49	5.73	5	60	5	1	2.5
MM9Z6V2B	8M	6.06	6.33	5	60	5	1	3
MM9Z6V8B	8N	6.65	6.93	5	40	5	0.5	3.5
MM9Z7V5B	8P	7.28	7.6	5	30	5	0.5	4
MM9Z8V2B	8Q	8.02	8.36	5	30	5	0.5	5
MM9Z9V1B	8R	8.85	9.23	5	30	5	0.5	6
MM9Z10B	8S	9.77	10.21	5	30	5	0.1	7
MM9Z11B	8T	10.76	11.22	5	30	5	0.1	8
MM9Z12B	8U	11.74	12.24	5	30	5	0.1	9
MM9Z13B	8V	12.91	13.49	5	37	5	0.1	10
MM9Z15B	8W	14.34	14.98	5	42	5	0.1	11
MM9Z16B	8X	15.85	16.51	5	50	5	0.1	12
MM9Z18B	8Y	17.56	18.35	5	65	5	0.1	13
MM9Z20B	8Z	19.52	20.39	5	85	5	0.1	15
MM9Z22B	9A	21.54	22.47	5	100	5	0.1	17
MM9Z24B	9B	23.72	24.78	5	120	5	0.1	19
MM9Z27B	9C	26.19	27.53	5	150	5	0.1	21
MM9Z30B	9D	29.19	30.69	5	200	5	0.1	23
MM9Z33B	9E	32.15	33.79	5	250	5	0.1	25
MM9Z36B	9F	35.07	36.87	5	300	5	0.1	27
MM9Z39B	9G	37	41	5	100	5	2	30

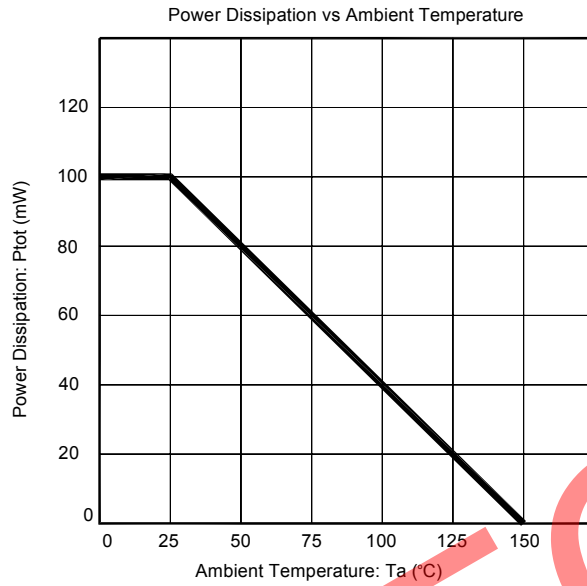
¹⁾ V_{ZT} is tested with pulses (20 ms).



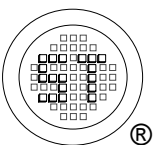
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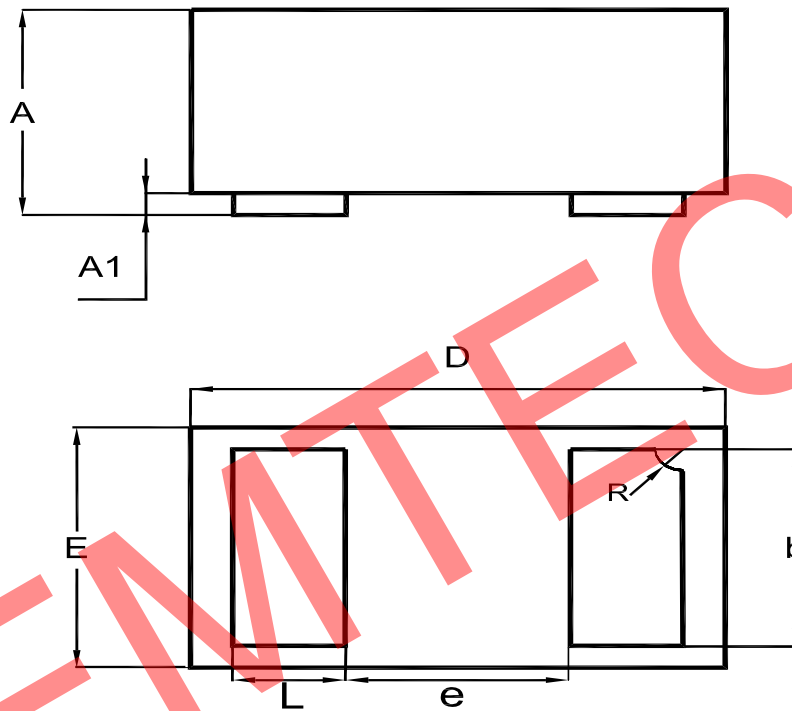


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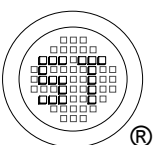
PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

DFN1006-2H



UNIT	A	A1	b	D	E	e	L	R
mm	0.51 0.46	0.05 0	0.55 0.45	1.075 0.95	0.675 0.55	0.4	0.3 0.2	0.15 0.05



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